Solid State Devices



Section 12 Occupation of States

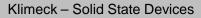
Gerhard Klimeck

gekco@purdue.edu

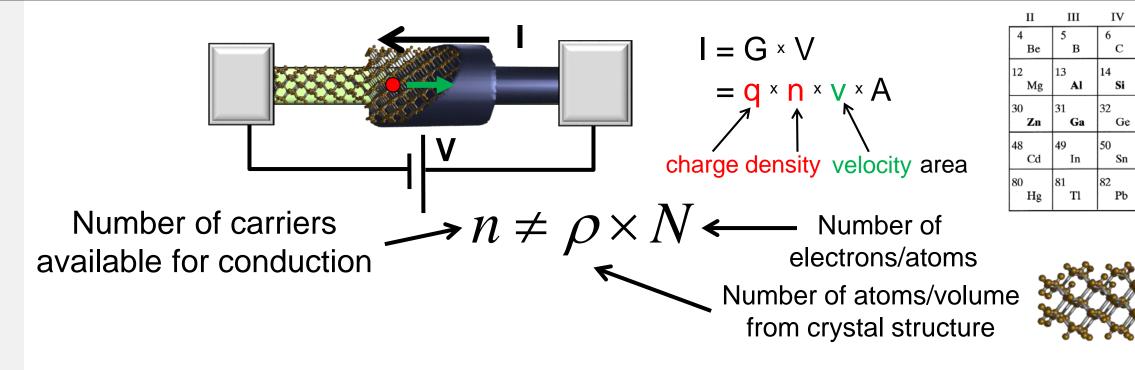


School of Electrical and Computer Engineering









- Materials, composition, crystals
- Tabulated for "known" bulk materials
- At nm-scale properties change with geometry => theory

Ν

Р

As

Sb

Bi

15

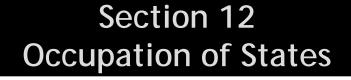
0

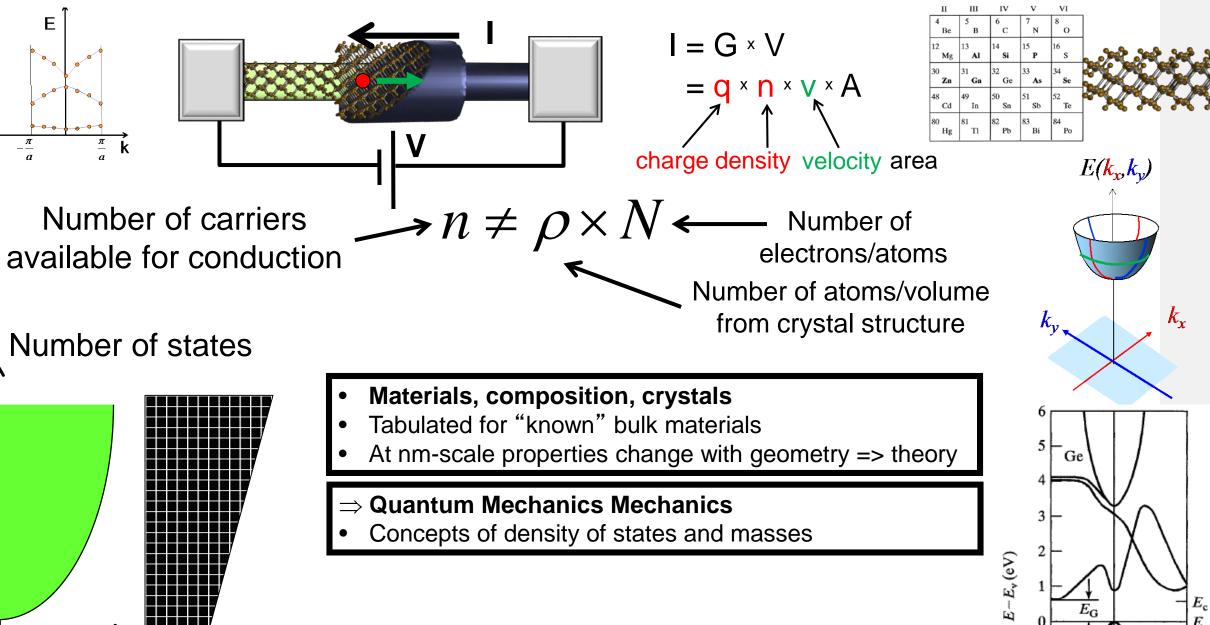
S

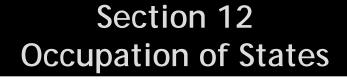
Se

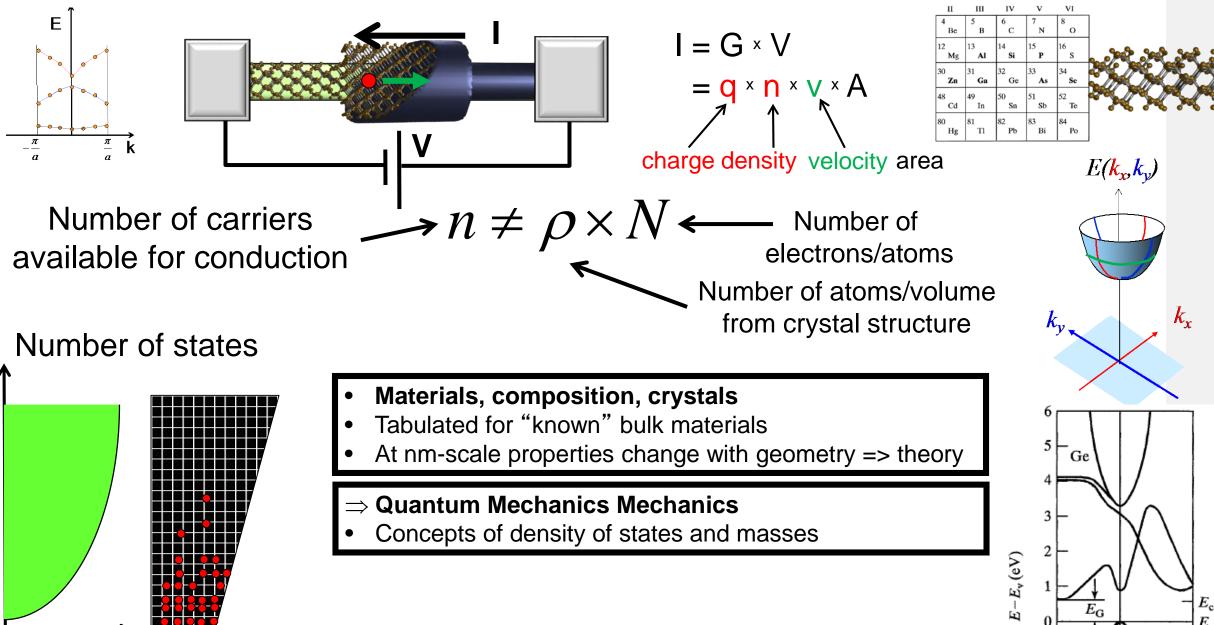
Te

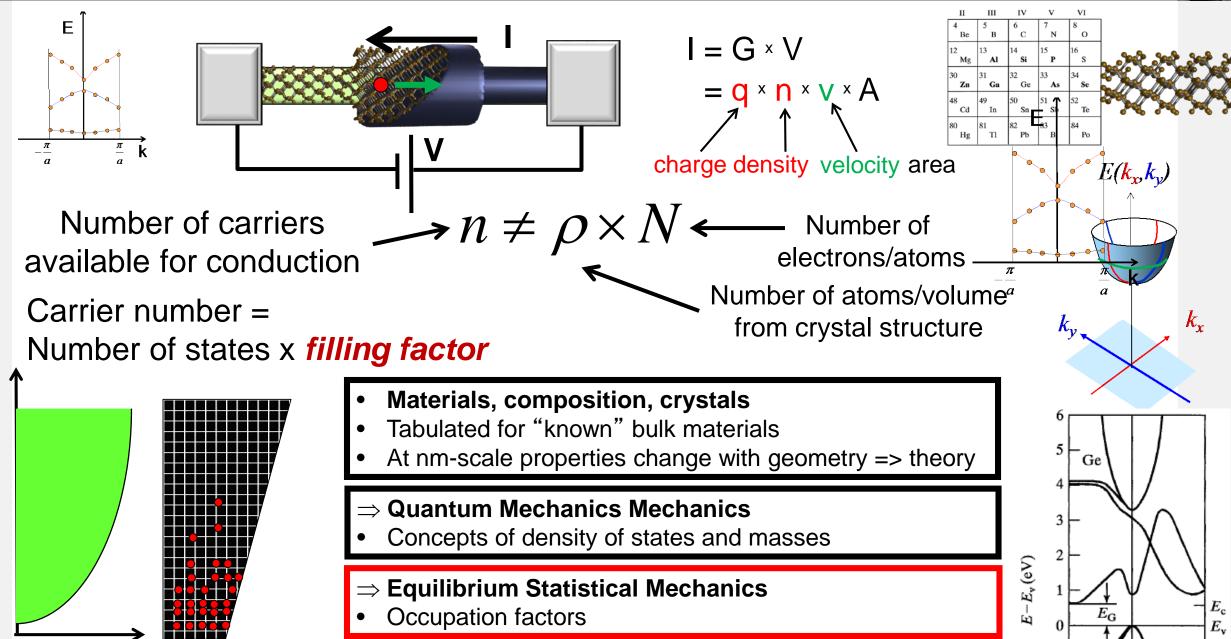
Po



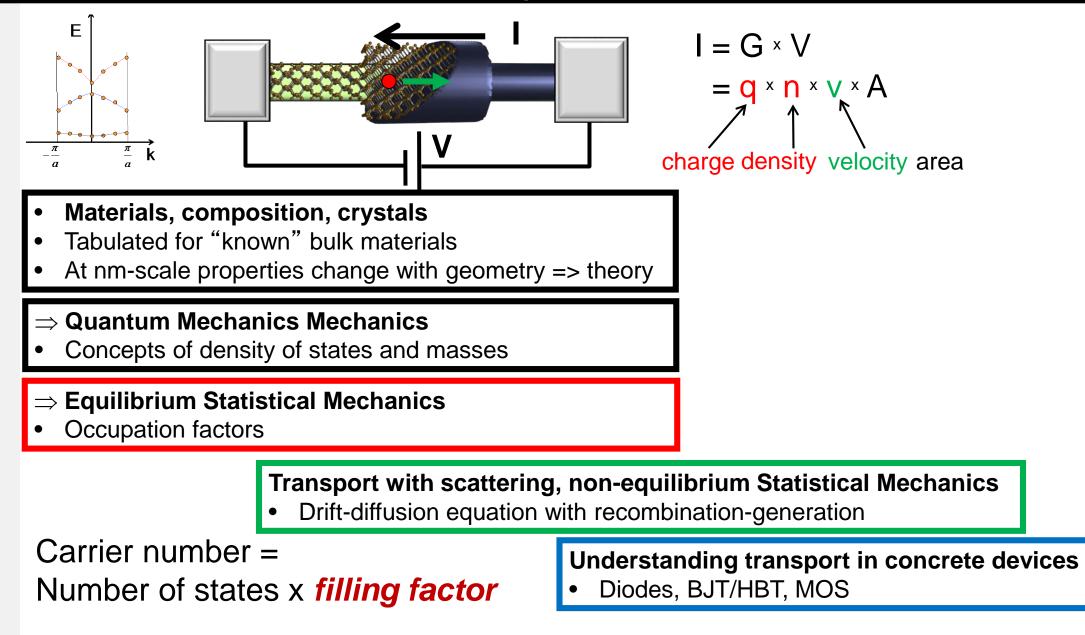




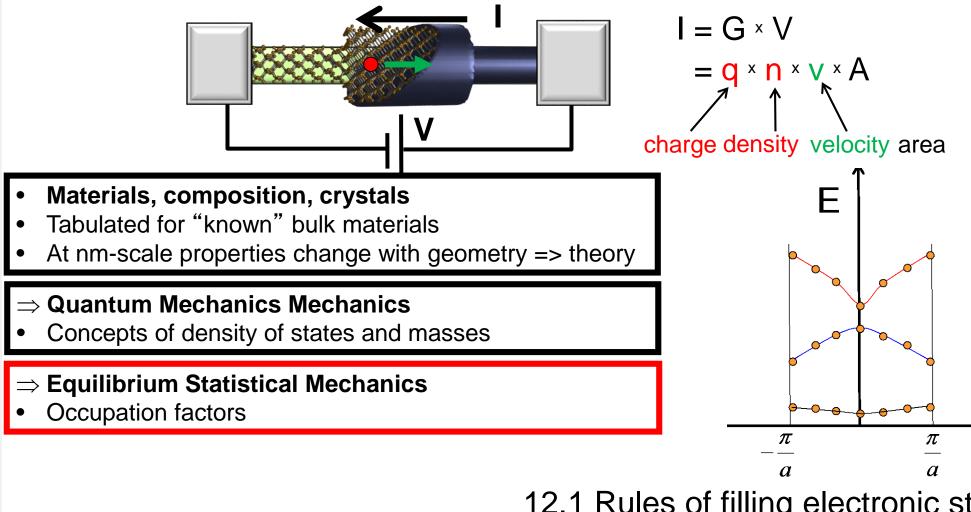












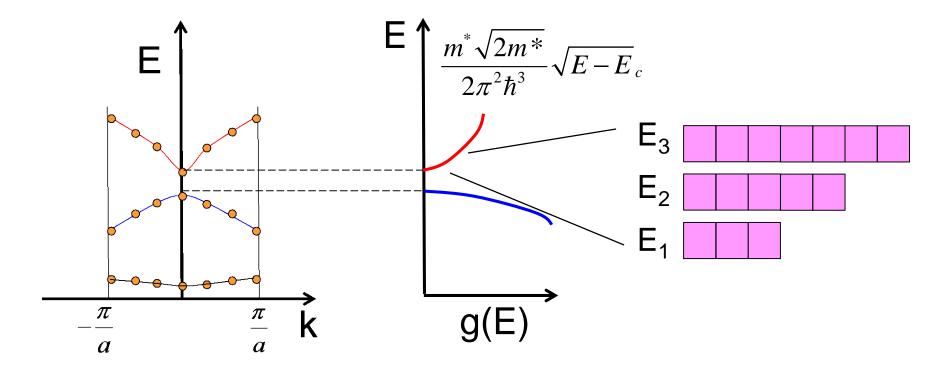
Carrier number = Number of states x *filling factor* 12.1 Rules of filling electronic states12.2 Three Derivations of Fermi-Dirac Statistics12.3 Intrinsic carrier concentration

E-k diagram and Electronic States





Density of States

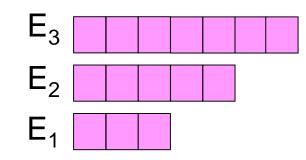






Rules for filling up the States





□ Pauli Principle: Only one electron per state

Total number of electrons is conserved

Total energy of the system is conserved

$$N_T = \sum_i N_i$$

$$d \quad E_T = \sum_i E_i N_i$$

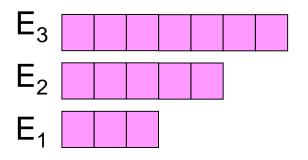




- 12.1 Rules of filling electronic states »Pauli exclusion
 - » Total particle conservation
 - » Total energy conservation



• 12.2 Derivation of Fermi-Dirac Statistics: three techniques



Carrier number =

Number of states x *filling factor*



One Video Segment

One Video Segment

• 12.3 Intrinsic carrier concentration

Reference: Vol. 6, Ch. 4

- 12.1 Rules of filling electronic states »Pauli exclusion
 - » Total particle conservation

One Video Segment

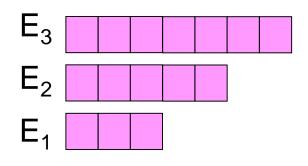
One Video Segment

One Video Segment

- »Total energy conservation
- 12.2 Derivation of Fermi-Dirac Statistics: three techniques
 - » Microcanonical ensemble statistics
 - » Detailed Balance thermal equilibrium & Pauli exclusion
 - » Partition Function statistical mechanics

Carrier number =

Number of states x *filling factor*



status

• 12.3 Intrinsic carrier concentration